

N-Channel Enhancement Mode MOSFET

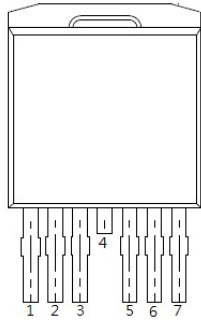
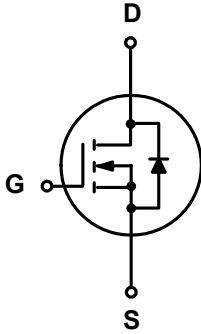
Features

Surface-mounted package
Super Trench
T_j max 175°C
Advanced trench cell design
MSL1

Applications

E- Tool appliances
BMS appliances
High power inverter system
Inverter appliances

1. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 <p>Top View TO-263-7L(D2PAK)</p>	
2,3	Source (S)		
4	Drain(D)		
5,6,7	Source (S)		

2. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C = 25 °C	85	-	V
V _{GS}	Gate-Source Voltage	T _C = 25 °C	-	±20	V
I _D ^{***}	Drain Current (DC)	T _C = 25 °C, V _{GS} = 10 V	-	220	A
		T _C = 100 °C, V _{GS} = 10 V	-	156	A
I _{DM} ^{*,***}	Drain Current (Pulsed)	T _C = 25 °C, V _{GS} = 10 V	-	800	A
P _{tot}	Drain power dissipation	T _C = 25 °C	-	250	W
T _{stg}	Storage Temperature		-55	175	°C
T _J	Junction Temperature		-	175	°C
I _S	Continuous-Source Current	T _C = 25 °C	-	220	A
E _{AS}	Single Pulsed Avalanche Energy	V _{DD} =100V , L=0.1mH	-	805	mJ
R _{θJA} ^{**}	Thermal Resistance- Junction to Ambient		-	32	°C/W
R _{θJC} ^{**}	Thermal Resistance- Junction to Case		-	0.45	

Notes :

- * Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- ** Surface Mounted on minimum footprint pad area.
- *** Limited by bonding wire

6. Electrical Characteristics ($T_A=25^\circ$ Unless Otherwise Noted)

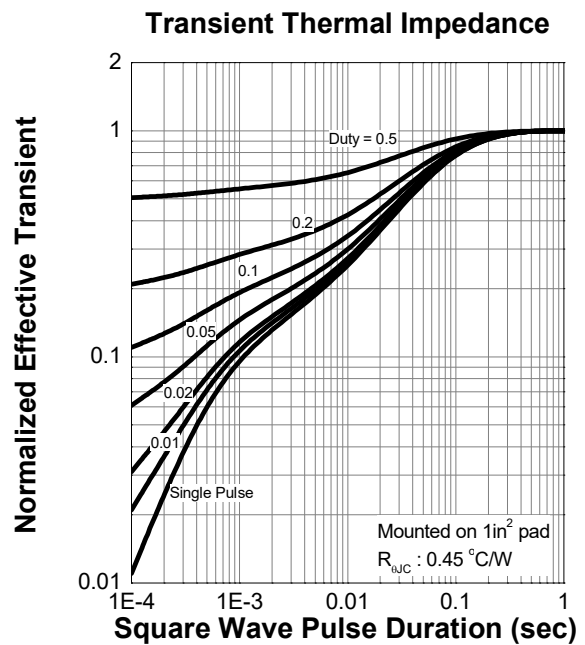
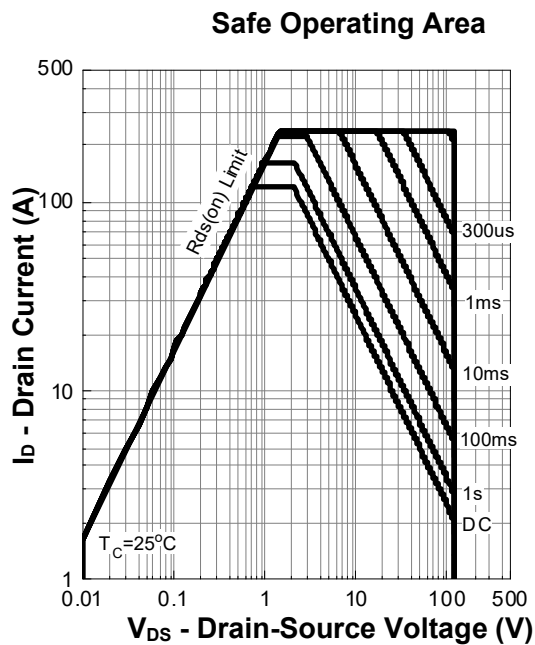
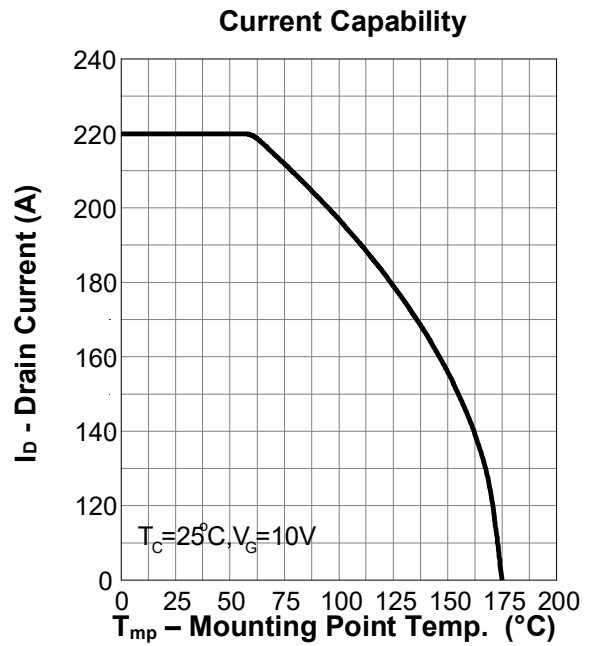
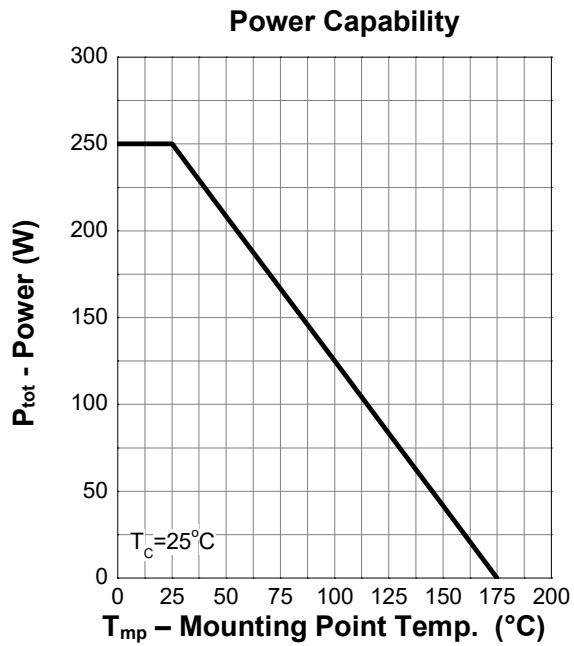
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_{DS} = 250\ \mu\text{A}$	85	95	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250\ \mu\text{A}$	2	-	4	V
I_{DSS}	Drain Leakage Current	$V_{DS} = 85\text{V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$T_J = 85^\circ\text{C}$	-	-	30	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
$R_{DS(on)}^a$	On-State Resistance	$V_{GS} = 10\text{ V}, I_{DS} = 30\text{ A}$	-	2.0	2.6	m Ω
Diode Characteristics						
V_{SD}^a	Diode Forward Voltage	$I_{SD} = 30\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_{DS} = 30\text{ A}, V_{GS} = 0\text{ V}$ $di_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	78	-	nS
Q_{rr}	Reverse Recovery Charge		-	110	-	nC
Dynamic Characteristics^b						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$ Frequency = 1 MHz	-	6234	-	pF
C_{oss}	Output Capacitance		-	1180	-	
C_{rss}	Reverse Transfer Capacitance		-	97	-	
$t_{d(on)}$	Turn-on Delay Time	$V_{DS} = 40\text{ V}, V_{GEN} = 10\text{ V},$ $R_G = 4.5\ \Omega, R_L = 1.3\ \Omega,$ $I_{DS} = 30\text{ A}$	-	41	-	nS
t_r	Turn-on Rise Time		-	68	-	
$t_{d(off)}$	Turn-off Delay Time		-	76	-	
t_f	Turn-off Fall Time		-	44	-	
Gate Charge Characteristics^b						
Q_g	Total Gate Charge	$V_{DS} = 40\text{ V}, V_{GS} = 10\text{ V},$ $I_{DS} = 30\text{ A}$	-	124	-	nC
Q_{gs}	Gate-Source Charge		-	31.2	-	
Q_{gd}	Gate-Drain Charge		-	39.2	-	

Notes :

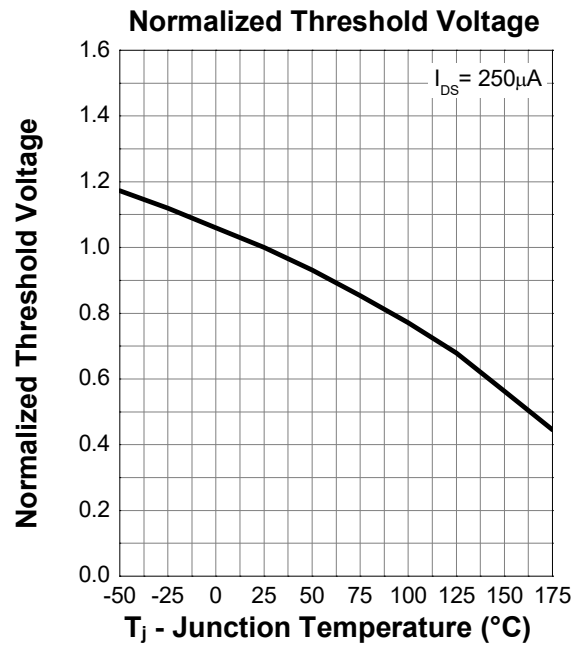
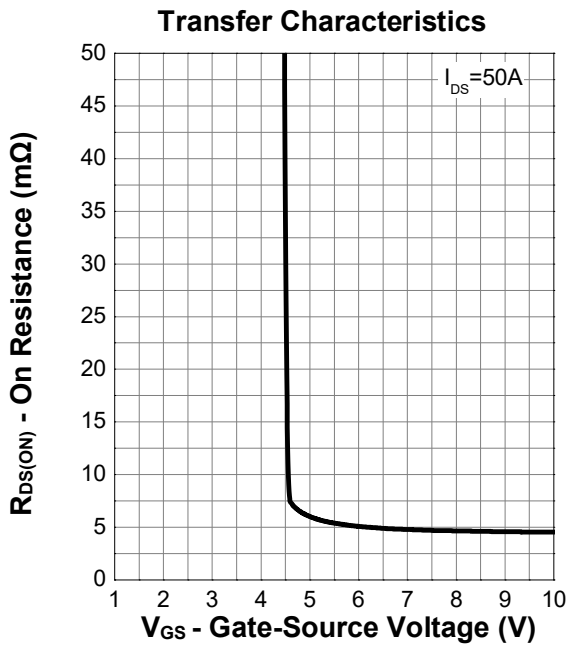
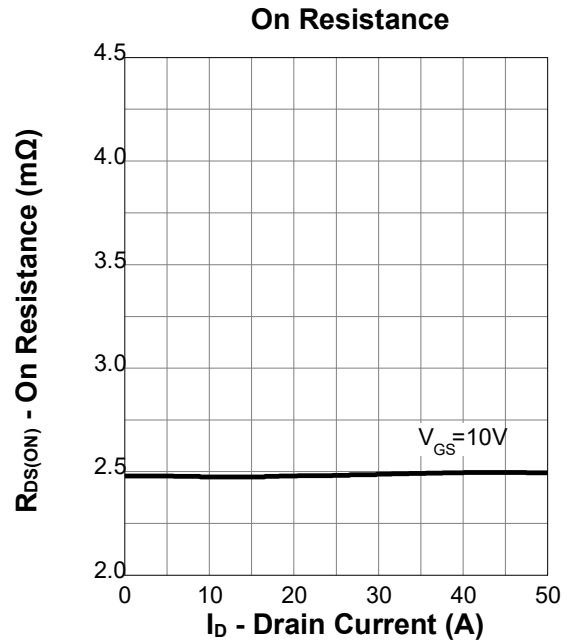
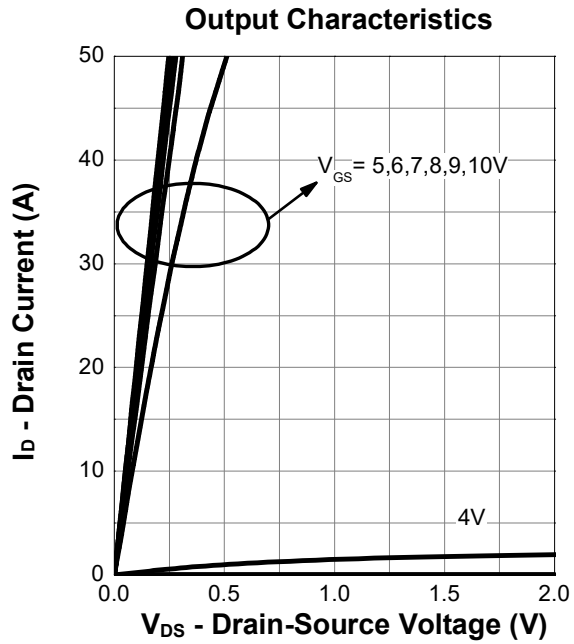
a : Pulse test ; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing

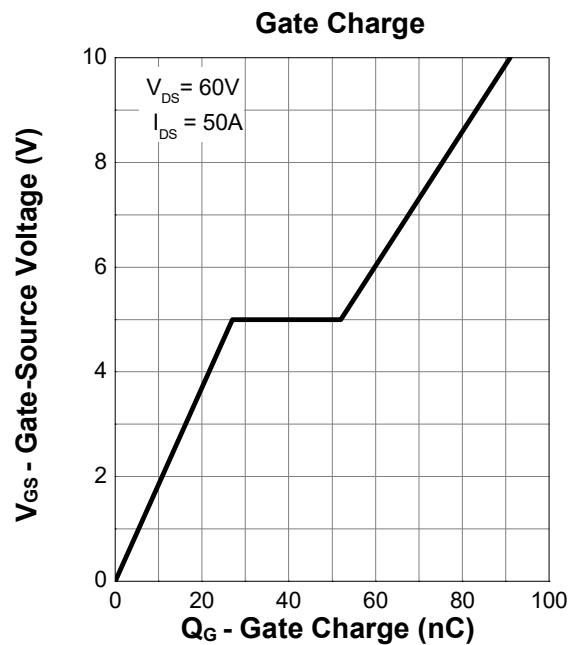
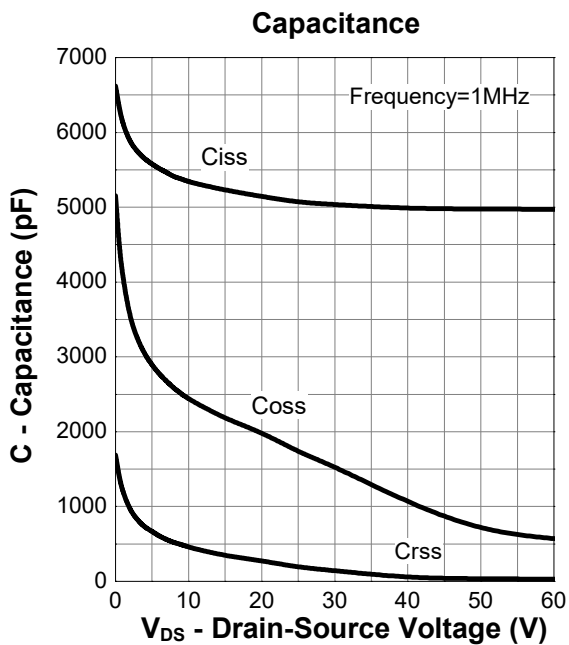
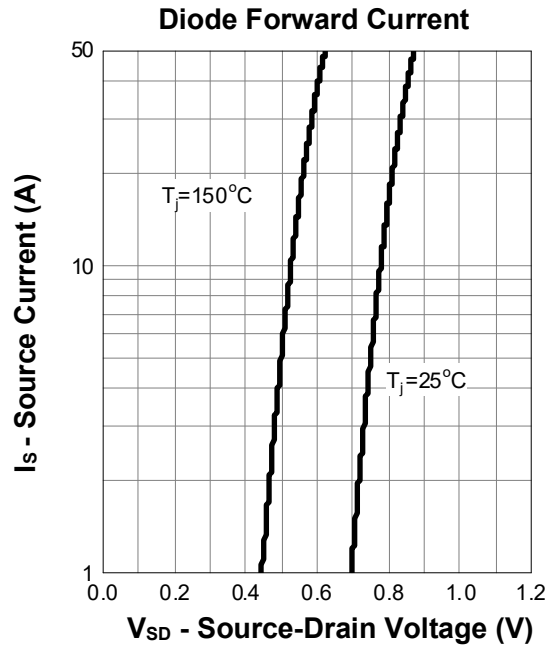
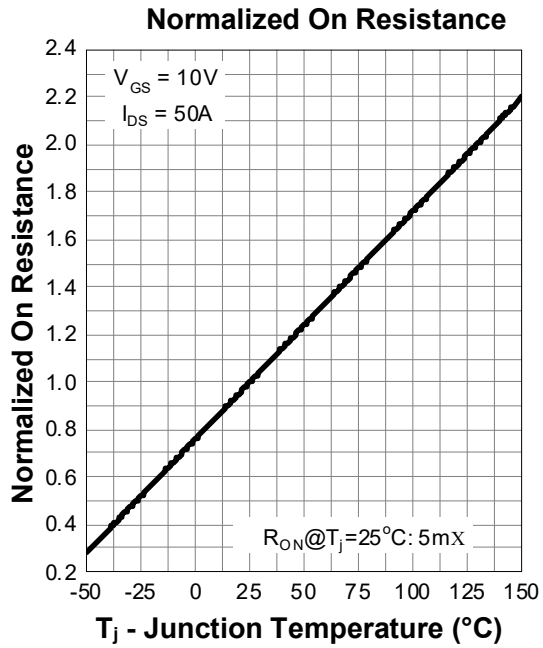
7. Typical Characteristics



7. Typical Characteristics (cont.)

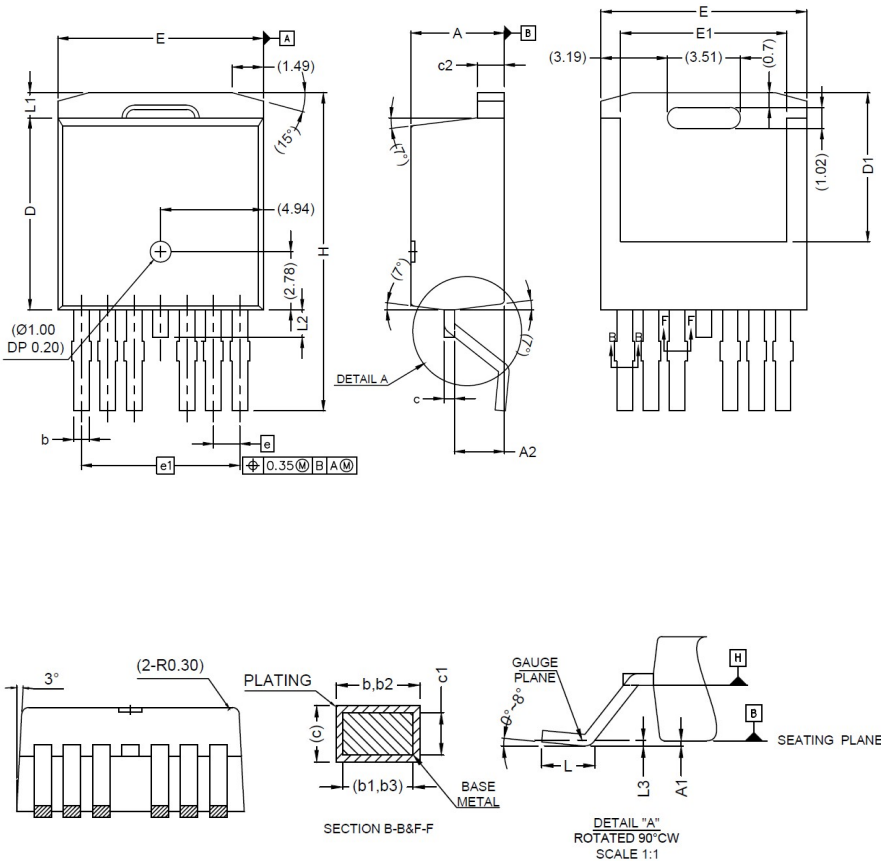


7. Typical Characteristics (cont.)



8. Package Dimensions

TO-263-7L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	4.30	4.70
A1	-	0.25
A2	2.20	2.60
b	0.65	0.85
b1	0.65	0.80
b2	0.80	1.00
b3	0.80	0.95
c	0.45	0.60
c1	0.45	0.55
c2	1.25	1.40
D	9.00	9.40
D1	6.86	7.42
E	9.68	10.08
E1	7.70	8.30
e	1.27 BSC	
e1	7.62 BSC	
L	1.78	2.79
L1	-	1.60
L2	-	1.78
L3	0.25BSD	
H	14.61	15.88